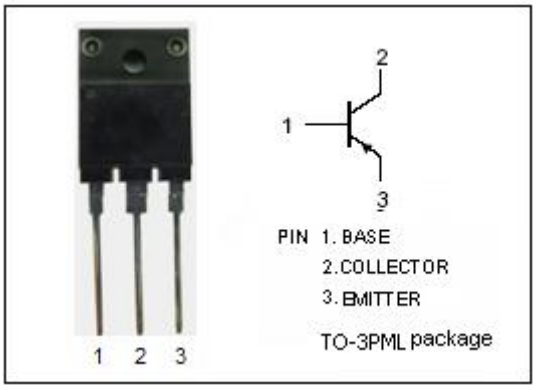
isc Silicon PNP Power Transistor 2SA1513

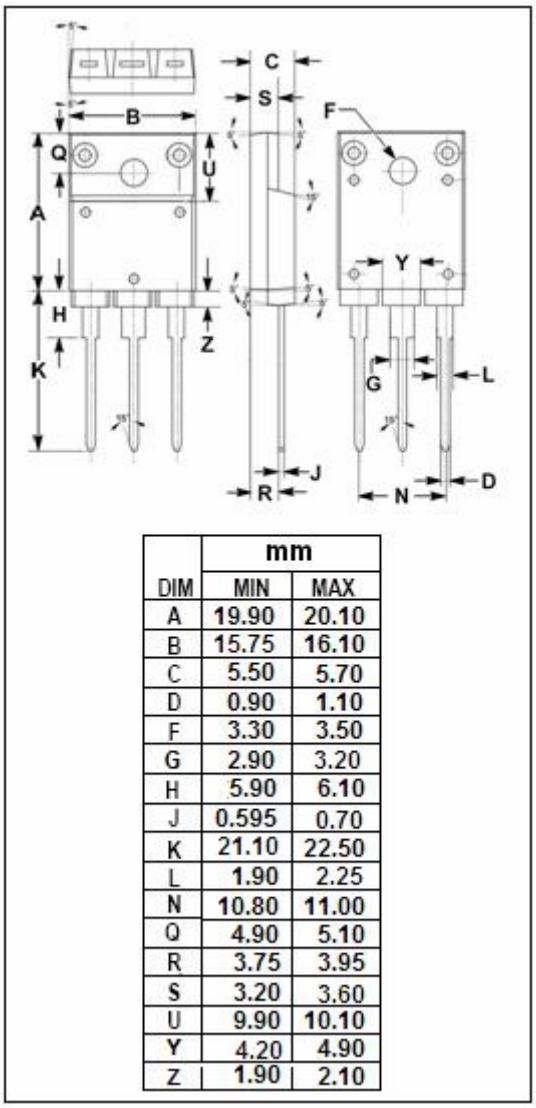


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -60V(Min)
- High Currrent Capacity
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -0.5V(Max.)@ I_C= -12A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high speed and high power switching applications.



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-15	A
P_C	Collector Power Dissipation @ T_C=25℃	60	W
	Collector Power Dissipation @ T_a=25℃	3.5	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon PNP Power Transistor 2SA1513

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -12A; I_B= -0.6A			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -12A; I_B= -0.6A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -3A; V_{CE}= -2V	100		400	
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f_{test}= 1.0MHz		300		pF
f_T	Current-Gain—Bandwidth Product	I_C= -1.5A; V_{CE}= -10V		80		MHz